

Silicon NPN Power Transistors

2SC1034

DESCRIPTION

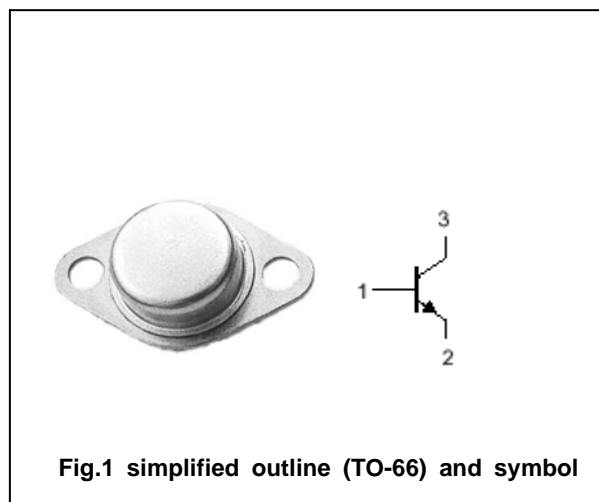
- With TO-66 package
- High breakdown voltage

APPLICATIONS

- For horizontal deflection output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = ^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1100	V
V_{EBO}	Emitter-base voltage	Open collector	13	V
I_C	Collector current		1	A
P_C	Collector power dissipation	$T_C = 25^\circ\text{C}$	25	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =10mA; I _E =0	1100			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =5mA; I _C =0	13			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =750mA; I _B =75mA			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =750mA; I _B =75mA			1.4	V
I _{CBO}	Collector cut-off current	V _{CB} =50V; I _E =0			0.2	mA
		V _{CB} =800V; I _E =0			5.0	
I _{EBO}	Emitter cut-off current	V _{EB} =8V; I _C =0			4	mA
h _{FE}	DC current gain	I _C =750mA; V _{CE} =3V	4		40	
f _T	Transition frequency	I _E =-0.2A; V _{CE} =10V		5		MHz
C _{ob}	Output capacitance	I _E =0; V _{CB} =10V; f=1MHz		95		pF

PACKAGE OUTLINE

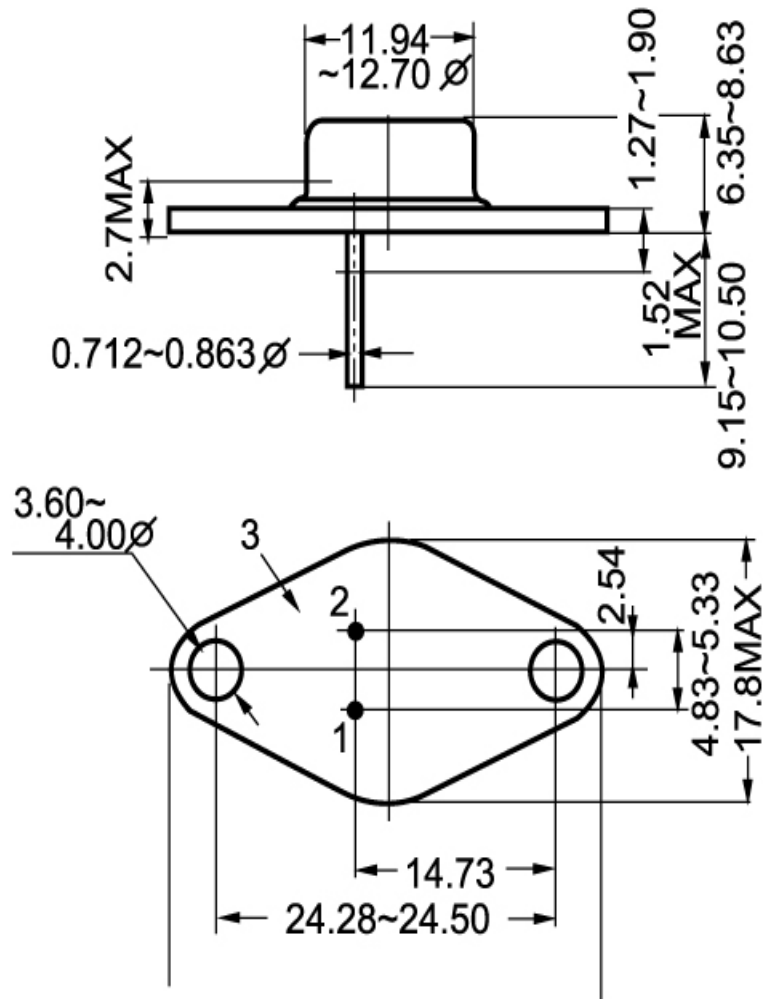


Fig.2 outline dimensions